

# MPSH10

Preferred Device

## VHF/UHF Transistors

### NPN Silicon

#### Features

- Pb-Free Packages are Available\*

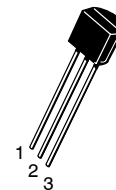
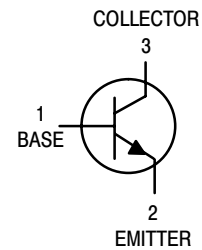
#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	$V_{CEO}$	25	Vdc
Collector - Base Voltage	$V_{CBO}$	30	Vdc
Emitter - Base Voltage	$V_{EBO}$	3.0	Vdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	350 2.8	W mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.0 8.0	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

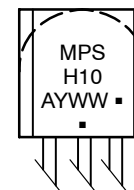
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200357	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



TO-92  
CASE 29-11  
STYLE 2

#### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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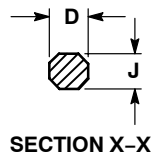
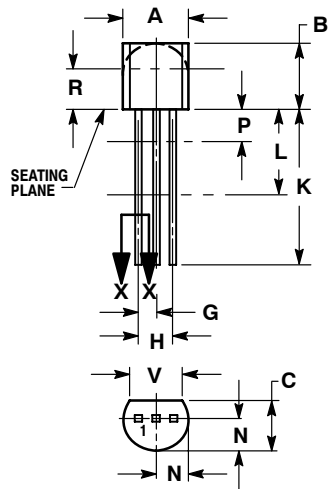
## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector – Emitter Breakdown Voltage ( $I_C = 1.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	25	–	Vdc
Collector – Base Breakdown Voltage ( $I_C = 100\ \mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	30	–	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10\ \mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	3.0	–	Vdc
Collector Cutoff Current ( $V_{CB} = 25\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	–	100	nAdc
Emitter Cutoff Current ( $V_{EB} = 2.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	100	nAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = 4.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ )	$h_{FE}$	60	–	–
Collector – Emitter Saturation Voltage ( $I_C = 4.0\text{ mA}$ , $I_B = 0.4\text{ mA}$ )	$V_{CE(sat)}$	–	0.5	Vdc
Base – Emitter On Voltage ( $I_C = 4.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ )	$V_{BE(on)}$	–	0.95	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Current – Gain – Bandwidth Product ( $I_C = 4.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	650	–	MHz
Collector – Base Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{cb}$	–	0.7	pF
Common – Base Feedback Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{rb}$	0.35	0.65	pF
Collector Base Time Constant ( $I_C = 4.0\text{ mA}$ , $V_{CB} = 10\text{ Vdc}$ , $f = 31.8\text{ MHz}$ )	$rb'C_c$	–	9.0	ps

# MPSH10

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AL



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

### STYLE 2:

1. BASE
2. EMITTER
3. COLLECTOR